

ABSTRACT OF THE DISCLOSURE

A method of fabricating a semiconductor epitaxial wafer having doped carbon includes the steps of mixing
5 a quantity of carbon with a quantity of silicon and then melting together the quantities of carbon and silicon, growing an ingot with carbon from the melted silicon containing carbon, grinding the ingot having carbon so as to produce a flat surface and a notch, slicing the
10 ingot having carbon into a piece of silicon wafer, polishing the silicon wafer having carbon, and growing an epitaxial silicon layer on a surface of the polished silicon wafer having carbon.

15